Growth mechanisms and origin of localized surface plas effects in Cu_{2â^'x}S thin films

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Citation Report

#	Article	IF	Citations
1	Plasmonic doped semiconductor nanocrystals: Properties, fabrication, applications and perspectives. Physics Reports, 2017, 674, 1-52.	10.3	252
2	Enhancement in the solar light harvesting ability of tungsten oxide thin films by annealing in vacuum and hydrogen. International Journal of Hydrogen Energy, 2017, 42, 28755-28765.	3.8	16
3	Phase Transformation and Evolution of Localized Surface Plasmon Resonance in Cu_{2â€“x}S Thin Films Deposited at 60 Â°C. Journal of Physical Chemistry C, 2017, 121, 25440-25446.	1.5	18
4	Structural, optical and electrical properties of copper antimony sulfide thin films grown by a citrate-assisted single chemical bath deposition. Applied Surface Science, 2018, 427, 1099-1106.	3.1	32
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8	Annealing induced phase transformation from amorphous to polycrystalline SnSe2 thin film photo detector with enhanced light-matter interaction. Journal of Non-Crystalline Solids, 2022, 578, 121353.	1.5	11
9	Epitaxial Engineering Strategy to Amplify Localized Surface Plasmon Resonance and Electrocatalytic Activity Enhancement in Layered Bismuth Selenide by Phosphorus Functionalization. Batteries and Supercaps, 2022, 5, .	2.4	5
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